



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

PCR 0.6 A Silicon Planar pnpn Thyristor

FEATURES

Current- I_{GT} : 120 μ A

I_{TRMS} : 0.6 A

V_{DRM} : 400 V

TO-92

1. CATHODE

2. GATE

3. ANODE



Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol		Test conditions	MIN	MAX	UNIT
On state voltage	V _{TM}		I _{TM} =0.6A		1.7	V
Gate trigger voltage	V _{GTF}		V _{AK} =7V		0.8	V
Repetitive peak off-state voltage	V _{DRM}		I _{DRM} = 10μA	400		V
Holding current	I _H		I _{HL} = 20mA , Av = 7 V		5	mA
Gate trigger current	I _{GTF}	A2	V _{AR} =7V	5	15	μA
		A1		15	30	μA
		A-1		30	45	μA
		A-2		45	60	μA
		A		60	80	μA
		B		80	120	μA